



浩畅半导体
www.szhaochang.cn

MMBT5401 TRANSISTOR (PNP)

SOT-23 Plastic-Encapsulate Transistors

产品规格书 承认书

客户确认:				公司签章:
部门	工程部	品保部	采购部	
签名				
日期				

SOT-23 Plastic-Encapsulate Transistors**MMBT5401 TRANSISTOR (PNP)****FEATURES**

- Complementary to MMBT5551
- Ideal for medium power amplification and switching

SOT-23

1. BASE
2. Emitter
3. Collector

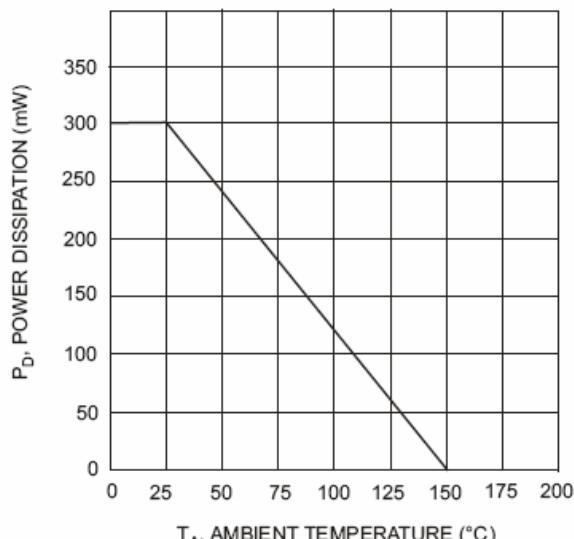
**MARKING: 2L****MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol Para	meter	Value	Units
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_c	Collector Current -Continuous	-0.6	A
P_c	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

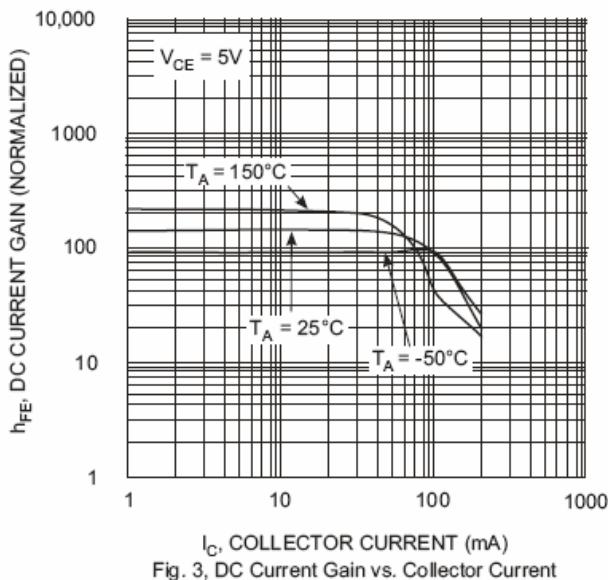
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-150		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -120\text{ V}, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$		-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	80		
	h_{FE2}	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	100	300	
	h_{FE3}	$V_{CE} = -5\text{V}, I_C = -50\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = -50\text{ mA}, I_B = -5\text{mA}$		-0.5	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C = -50\text{ mA}, I_B = -5\text{mA}$		-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 30\text{MHz}$	100		MHz

Typical Characteristics



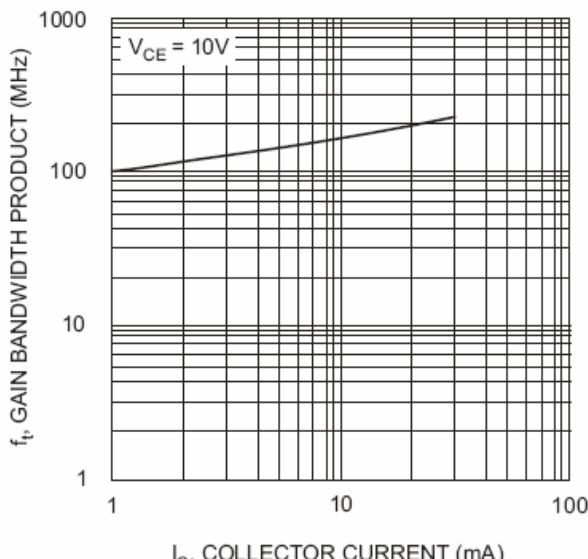
T_A , AMBIENT TEMPERATURE (°C)

Fig. 1, Max Power Dissipation vs
Ambient Temperature



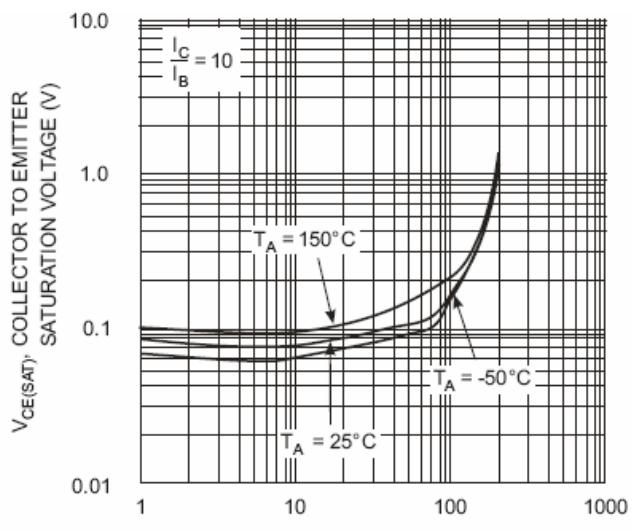
I_C , COLLECTOR CURRENT (mA)

Fig. 3, DC Current Gain vs. Collector Current

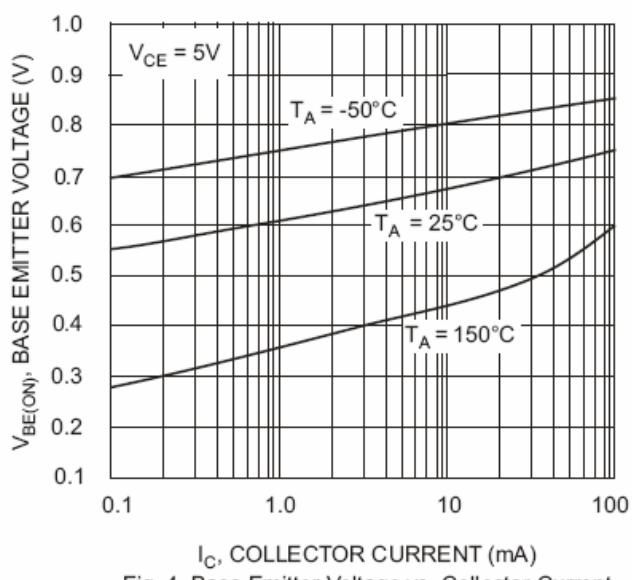


I_C , COLLECTOR CURRENT (mA)
Fig. 5, Gain Bandwidth Product vs Collector Current

MMBT5401

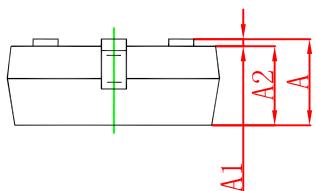
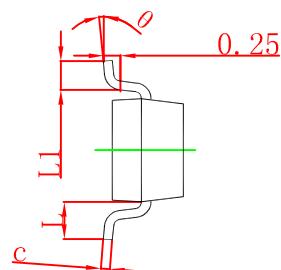
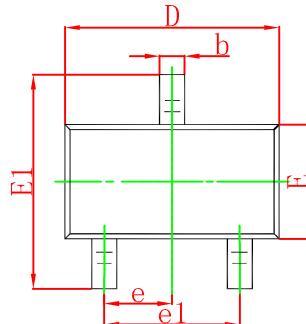


I_C , COLLECTOR CURRENT (mA)
Fig. 2, Collector Emitter Saturation Voltage
vs. Collector Current



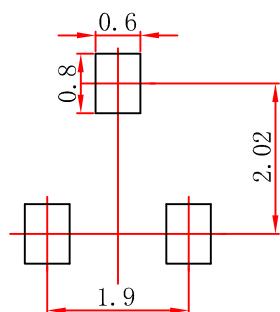
I_C , COLLECTOR CURRENT (mA)
Fig. 4, Base Emitter Voltage vs. Collector Current

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.